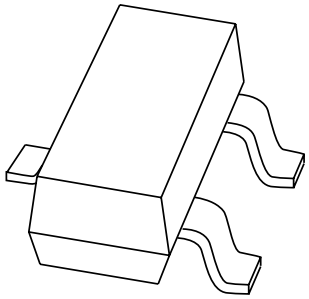
DATA SHEET



BAT54W series
Schottky barrier (double) diodes

Product specification
Supersedes data of October 1993

1996 Mar 19

Philips
Semiconductors

PHILIPS

Schottky barrier (double) diodes BAT54W series

FEATURES

- Low forward voltage
- Guard ring protected
- Very small SMD package.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Blocking diodes.

DESCRIPTION

Planar Schottky barrier diodes encapsulated in a SOT323 very small plastic SMD package. Single diodes and double diodes with different pinning are available.

MARKING

TYPE NUMBER	MARKING CODE
BAT54W	L4
BAT54AW	42
BAT54CW	43
BAT54SW	44

PINNING

PIN	BAT54			
	W	AW	CW	SW
1	a	k_1	a_1	a_1
2	n.c.	k_2	a_2	k_2
3	k	a_1, a_2	k_1, k_2	k_1, a_2

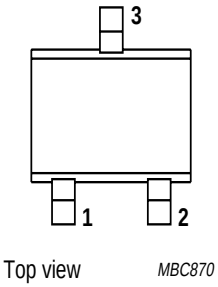


Fig.1 Simplified outline (SOT323) and pin configuration.

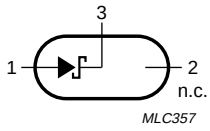


Fig.2 BAT54W single diode configuration (symbol).

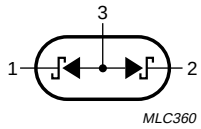


Fig.3 BAT54AW diode configuration (symbol).

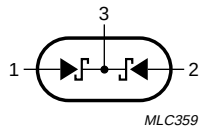


Fig.4 BAT54CW diode configuration (symbol).

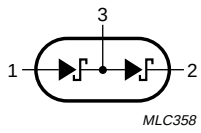


Fig.5 BAT54SW diode configuration (symbol).

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_R	continuous reverse voltage		–	30	V
I_F	continuous forward current		–	200	mA
I_{FRM}	repetitive peak forward current	$t_p \leq 1$ s; $\delta \leq 0.5$	–	300	mA
I_{FSM}	non-repetitive peak forward current	$t_p < 10$ ms	–	600	mA
P_{tot}	total power dissipation (per package)	$T_{amb} \leq 25$ °C	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	125	°C
T_{amb}	operating ambient temperature		–65	+125	°C

ELECTRICAL CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode				
V_F	forward voltage	see Fig.6		
		I_F = 0.1 mA	240	mV
		I_F = 1 mA	320	mV
		I_F = 10 mA	400	mV
		I_F = 30 mA	500	mV
		I_F = 100 mA	800	mV
I_R	reverse current	V_R = 25 V; note 1; see Fig.7	2	µA
t_{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA: see Fig.9	5	ns
C_d	diode capacitance	f = 1 MHz; V_R = 1 V; see Fig.8	10	pF

Note

1. Pulsed test: t_p = 300 µs; δ = 0.02.

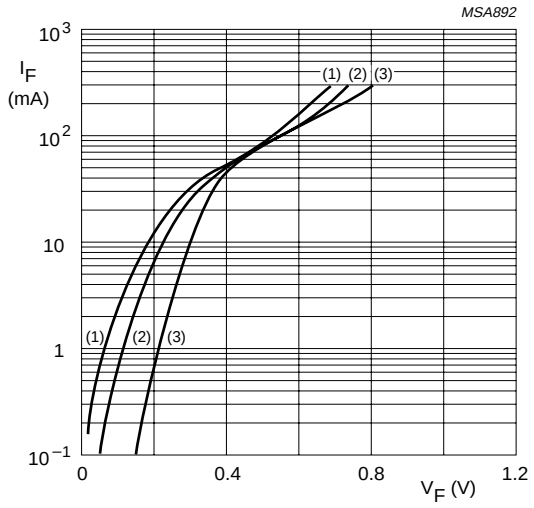
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

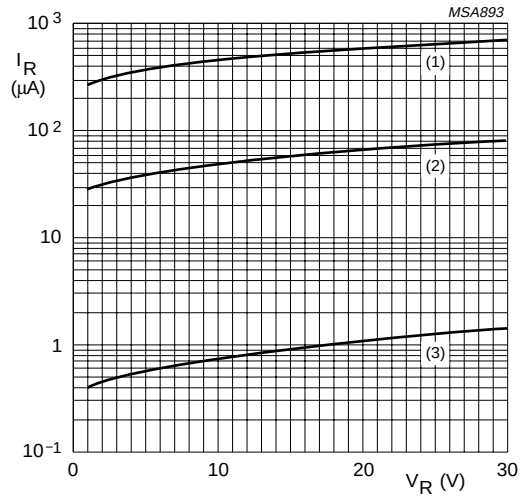
1. Refer to SOT323 standard mounting conditions.

GRAPHICAL DATA



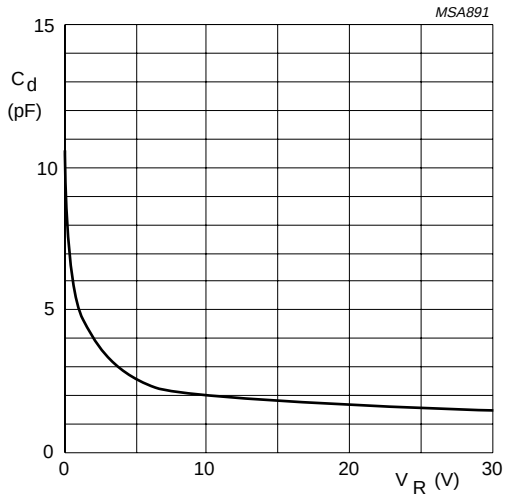
(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.

Fig.6 Forward current as a function of forward voltage; typical values.



(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.

Fig.7 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz; T_{amb} = 25 °C.

Fig.8 Diode capacitance as a function of reverse voltage; typical values.

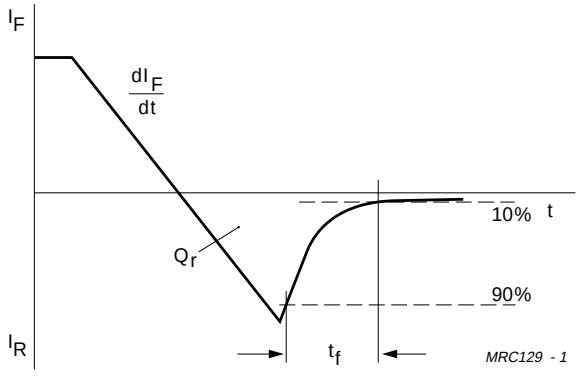


Fig.9 Reverse recovery definitions.